12 June 2014

Product data sheet

1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	18	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	51	W
Static characte	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 175 °C;$ Fig. 12; Fig. 13		-	-	154	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ Fig. 12; Fig. 13		-	65	77	mΩ
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 6 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	36	mJ



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G 4
mb	D	mounting base; connected to drain	1 3	mbb076 S
			DPAK (SOT428)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK7277-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7277-55A	BUK7277-55A

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

	Conditions		Min	Max	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	55	V
drain-gate voltage	R_{GS} = 20 k Ω		-	55	V
gate-source voltage			-20	20	V
total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	51	W
drain current	T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 2</u>		-	13	Α
	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	18	Α
peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3	[1]	-	73	Α
storage temperature			-55	175	°C
junction temperature			-55	175	°C
	drain-gate voltage gate-source voltage total power dissipation drain current peak drain current storage temperature junction temperature	$\begin{array}{ll} \text{drain-gate voltage} & R_{GS} = 20 \text{ k}\Omega \\ \\ \text{gate-source voltage} \\ \text{total power dissipation} & T_{mb} = 25 ^{\circ}\text{C}; \underline{\text{Fig. 1}} \\ \\ \text{drain current} & T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 10 \text{V}; \underline{\text{Fig. 2}} \\ \\ T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V}; \underline{\text{Fig. 2}}; \underline{\text{Fig. 3}} \\ \\ \text{peak drain current} & T_{mb} = 25 ^{\circ}\text{C}; \text{pulsed}; t_p \leq 10 \mu\text{s}; \underline{\text{Fig. 3}} \\ \\ \text{storage temperature} & \end{array}$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain diode						
I _S	source current	T _{mb} = 25 °C		-	18	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	73	Α
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 6 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	36	mJ

[1] Peak drain current is limited by chip, not package.

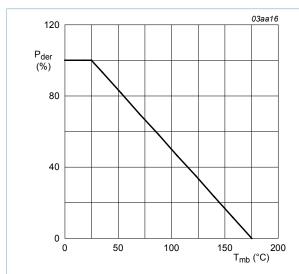


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

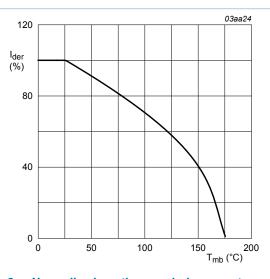


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$

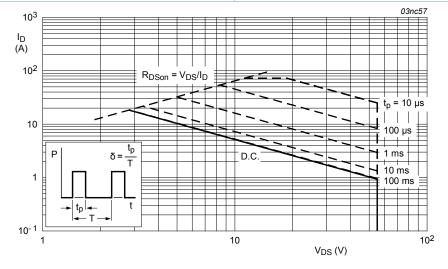


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25$ °C; I_{DM} is single pulse

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	-	2.9	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; FR4 board	-	71.4	-	K/W

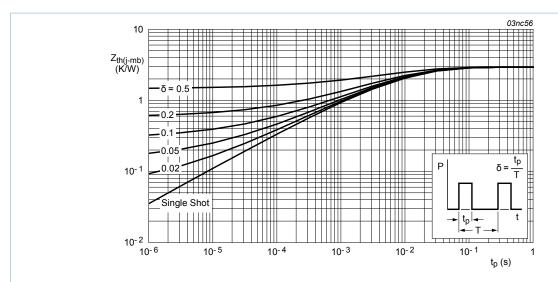


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$	50	-	-	V
V _{GS(th)} gate-source t voltage	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 11	2	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 11	-	-	4.4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 11	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
		V _{DS} = 55 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; Fig. 12; Fig. 13	-	-	154	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 12; Fig. 13	-	65	77	mΩ
Dynamic ch	naracteristics					
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 14</u>	-	316	422	pF
C _{oss}	output capacitance		-	92	110	pF
C _{rss}	reverse transfer capacitance		-	64	87	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_{L} = 1.2 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω ; T_{j} = 25 °C	-	10	-	ns
t _r	rise time		-	50	-	ns
t _{d(off)}	turn-off delay time		-	70	-	ns
t _f	fall time		-	40	-	ns
L _D	internal drain inductance	measured from drain lead from package to centre of die; $T_j = 25 ^{\circ}\text{C}$	-	2.5	-	nH
L _S	internal source inductance	measured from source lead from package to source bond pad; T _j = 25 °C	-	7.5	-	nН
Source-drai	in diode		1		'	
V _{SD}	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 15$	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	32	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	120	-	nC

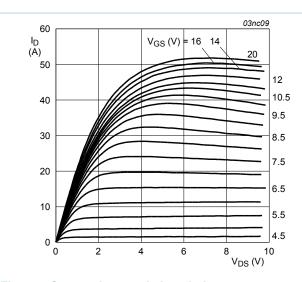


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values



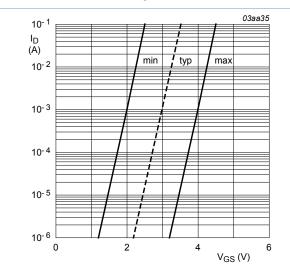


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

$$T_j=25\,^{\circ}C; V_{DS}=5V$$

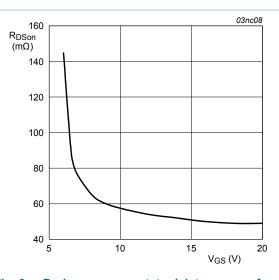


Fig. 6. Drain-source on-state risistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 10A$$

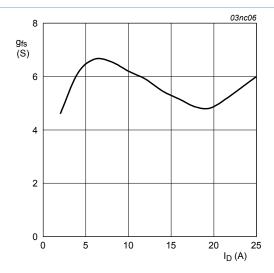


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25^{\circ}C; V_{DS} = 25V$$

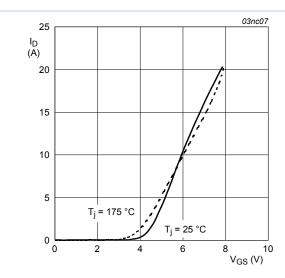


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



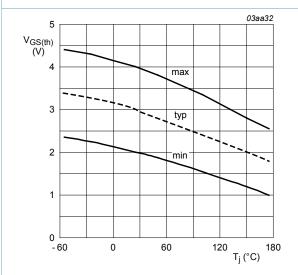


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 mA; V_{DS} = V_{GS}$$

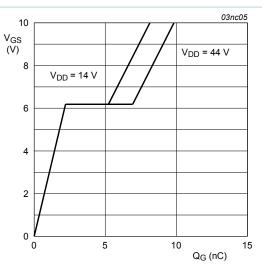


Fig. 10. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 10A$$

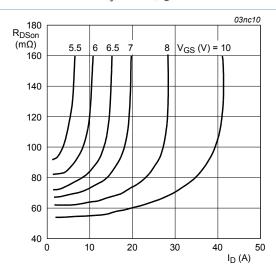


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

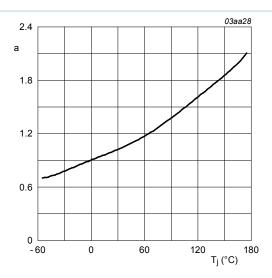


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

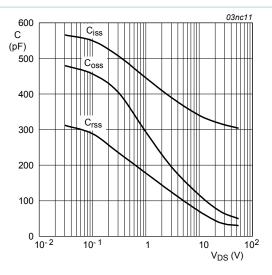


Fig. 14. Input, output and reverse capicitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

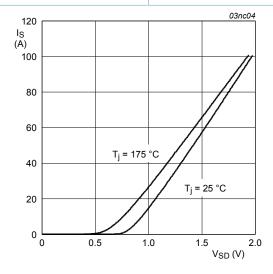
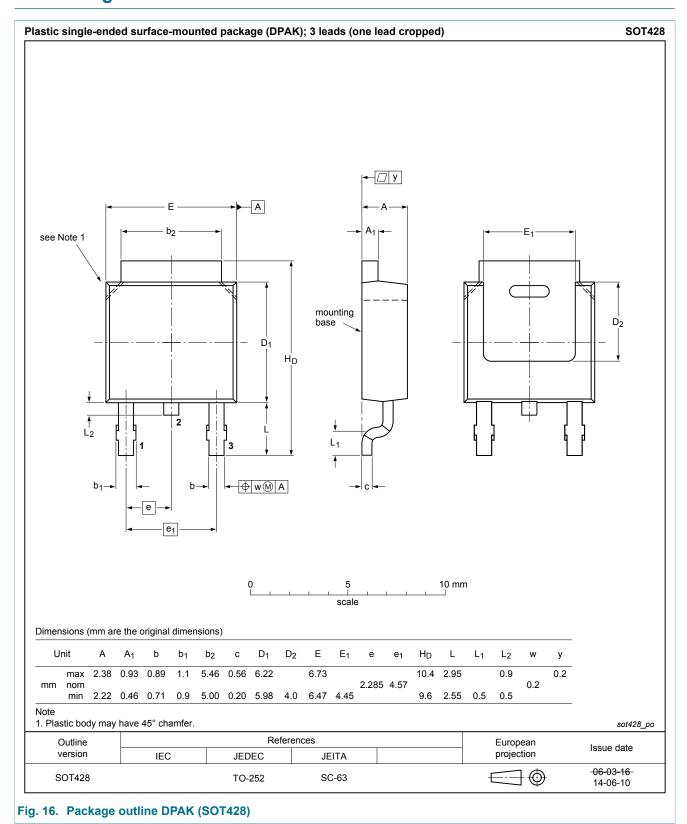


Fig. 15. Reverse diode current as a function of reverse dioode voltage; typical values

$$V_{\it GS} = 0V$$

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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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